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(54) Title: MEMORY CELL HAVING DIELECTRIC MEMORY ELEMENT

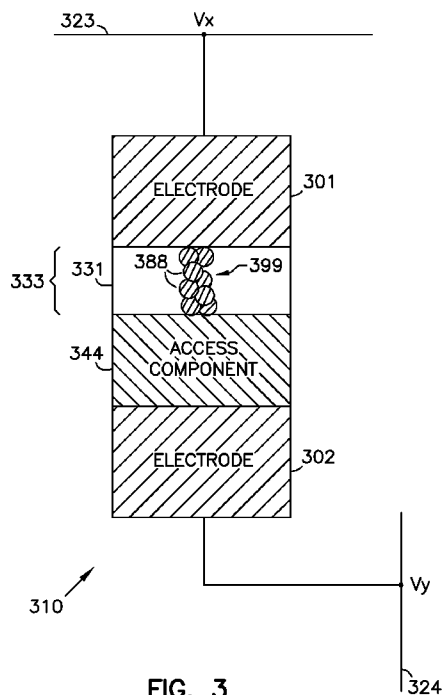


FIG. 3

(57) Abstract: Some embodiments include apparatus and methods having a memory cell with a first electrode, a second electrode, and a dielectric located between the first and second electrodes. The dielectric may be configured to allow the memory cell to form a conductive path in the dielectric from a portion of a material of the first electrode to represent a first value of information stored in the memory cell. The dielectric may also be configured to allow the memory cell to break the conductive path to represent a second value of information stored in the memory cell.



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